

### IGBT module

#### **SKiiP 38GB12F4V19**

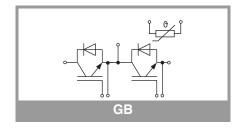
Target Data

#### **Features**

- Fast Trench 4 IGBTs
- SiC Diodes
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Absolute	Maximum Ratings	S		
Symbol	Conditions		Values	Unit
Inverter -	IGBT			
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		1200	V
Ic	$\lambda_{paste}$ =0.8 W/(mK) T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	303	Α
		T <sub>s</sub> = 70 °C	243	Α
P	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	361	Α
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	291	Α
I <sub>Cnom</sub>			300	А
I <sub>CRM</sub>	I <sub>CRM</sub> = 3 x I <sub>Cnom</sub>		900	Α
$V_{GES}$			-20 20	V
t <sub>psc</sub>	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T <sub>j</sub> = 150 °C	10	μs
Tj			-40 175	°C
Inverse -	Diode			
l <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	133	Α
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	108	Α
l <sub>F</sub>	$\lambda_{paste}$ =2.5 W/(mK) T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	148	Α
		T <sub>s</sub> = 70 °C	120	Α
I <sub>Fnom</sub>			80	Α
I <sub>FRM</sub>			224	Α
I <sub>FSM</sub>	10 ms, sin 180°, T <sub>j</sub> = 150 °C		212	Α
Tj			-40 175	°C
Module				
I <sub>t(RMS)</sub>	T <sub>terminal</sub> = 80 °C, 20	A per spring	t.b.d.	Α
T <sub>stg</sub>			-40 125	°C
V <sub>isol</sub>	AC sinus 50 Hz, t = 1 min		2500	V

Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
Inverter -	IGBT		•			•
V <sub>CE(sat)</sub>	I <sub>C</sub> = 300 A	T <sub>j</sub> = 25 °C		2.05	2.42	V
	V <sub>GE</sub> = 15 V chiplevel	T <sub>j</sub> = 150 °C		2.59	2.96	V
V <sub>CE0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.10	1.28	V
		T <sub>j</sub> = 150 °C		0.95	1.13	V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V chiplevel	T <sub>j</sub> = 25 °C		3.2	3.8	$m\Omega$
		T <sub>j</sub> = 150 °C		5.5	6.1	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 10.4$ mA		5.2	5.8	6.4	V
I <sub>CES</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 12$	200 V, T <sub>j</sub> = 25 °C		0.1	1.6	mA
C <sub>ies</sub>	V <sub>CF</sub> = 25 V	f = 1 MHz		17.60		nF
Coes	$V_{CE} = 25 \text{ V}$	f = 1 MHz		1.16		nF
C <sub>res</sub>	- VGE - VV	f = 1 MHz		0.94		nF
$Q_{G}$	- 8 V+ 15 V			1700		nC
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C			0		Ω
t <sub>d(on)</sub>	$V_{CC} = 600 \text{ V}$	T <sub>j</sub> = 150 °C				ns
t <sub>r</sub>	I <sub>C</sub> = 300 A	T <sub>j</sub> = 150 °C				ns
E <sub>on</sub>		T <sub>j</sub> = 150 °C		10		mJ
t <sub>d(off)</sub>		T <sub>j</sub> = 150 °C				ns
t <sub>f</sub>		T <sub>j</sub> = 150 °C				ns
E <sub>off</sub>	V <sub>GE</sub> = +15/-15 V	T <sub>j</sub> = 150 °C		22		mJ
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =0.8 W/(mK)			0.16		K/W
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =2.5 W/(mK)			0.12		K/W





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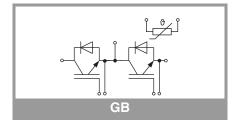
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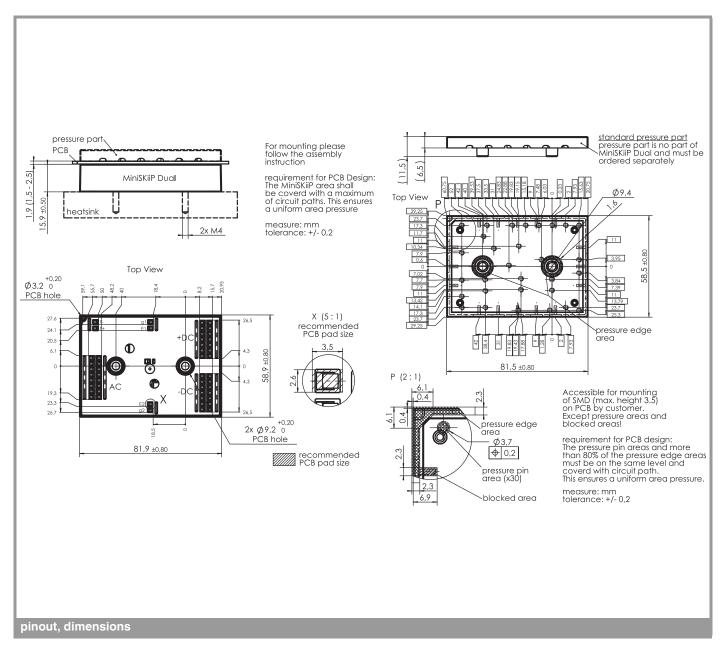
Target Data

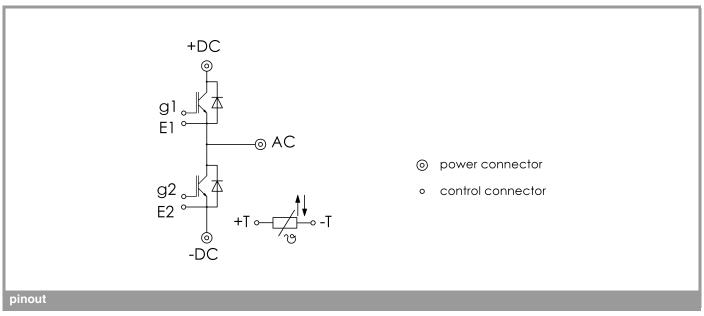
#### **Features**

- Fast Trench 4 IGBTs
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Characteristics									
Symbol	Conditions	min.	typ.	max.	Unit				
Inverse - Diode									
$V_F = V_{EC}$	I <sub>F</sub> = 80 A	T <sub>j</sub> = 25 °C		1.40	1.60	V			
	V <sub>GE</sub> = 0 V chiplevel	T <sub>j</sub> = 150 °C		1.80	2.10	٧			
$V_{F0}$	chiplevel	T <sub>j</sub> = 25 °C		0.95	1.05	V			
	Chipievei	T <sub>j</sub> = 150 °C		0.83	0.90	V			
r <sub>F</sub>	chiplevel	T <sub>j</sub> = 25 °C		5.6	6.9	mΩ			
		T <sub>j</sub> = 150 °C		12	15	mΩ			
I <sub>RRM</sub>	$I_F = 80 \text{ A}$ $di/dt_{off} = 500 \text{ A/}\mu\text{s}$ $V_{GE} = -15 \text{ V}$ $V_{CC} = 600 \text{ V}$	T <sub>j</sub> = 150 °C		-		Α			
$Q_{rr}$		T <sub>j</sub> = 150 °C		-		μC			
E <sub>rr</sub>		T <sub>j</sub> = 150 °C		-		mJ			
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0.8 W/(mK)			0.36		K/W			
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =2.5 W/(mK)			0.3		K/W			
Module									
L <sub>CE</sub>				15		nΗ			
Ms	to heat sink		2		2.5	Nm			
W				76		g			
Temperature Sensor									
R <sub>100</sub>	T <sub>c</sub> =100°C (R <sub>25</sub> =5 kΩ)			493 ± 5%		Ω			
B <sub>25/85</sub>	$R_{(T)}=R_{25}*exp[B_{25/85}*(1/T-1/298)], [T]=K$		3420			K			







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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FF600R12IP4V FF800R17KP4\_B2 FF900R12IE4V MIXA30W1200TED MIXA450PF1200TSF FP06R12W1T4\_B3 FP100R07N3E4

FP100R07N3E4\_B11 FP10R06W1E3\_B11 FP10R12W1T4\_B11 FP10R12YT3 FP10R12YT3\_B4 FP150R07N3E4 FP15R12KT3

FP15R12W2T4